

CMLD4448

**SURFACE MOUNT
DUAL, ISOLATED
HIGH SPEED SILICON
SWITCHING DIODES**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD4448 type contains two (2) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for high speed switching applications.

MARKING CODE: C48

PICOmini™



SOT-563 CASE

MAXIMUM RATINGS: (T_A=25°C)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, tp=1.0µs
Peak Forward Surge Current, tp=1.0s
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V _R RM	120
I _F	250
I _{FRM}	500
I _{FSM}	4.0
I _{FSM}	1.0
P _D	250
T _J , T _{stg}	-65 to +150
θ _{JA}	500

UNITS

V
mA
mA
A
A
mW
°C
°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

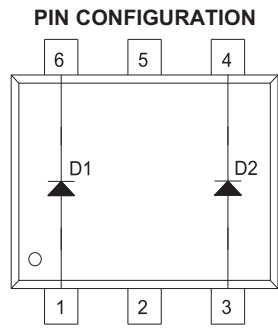
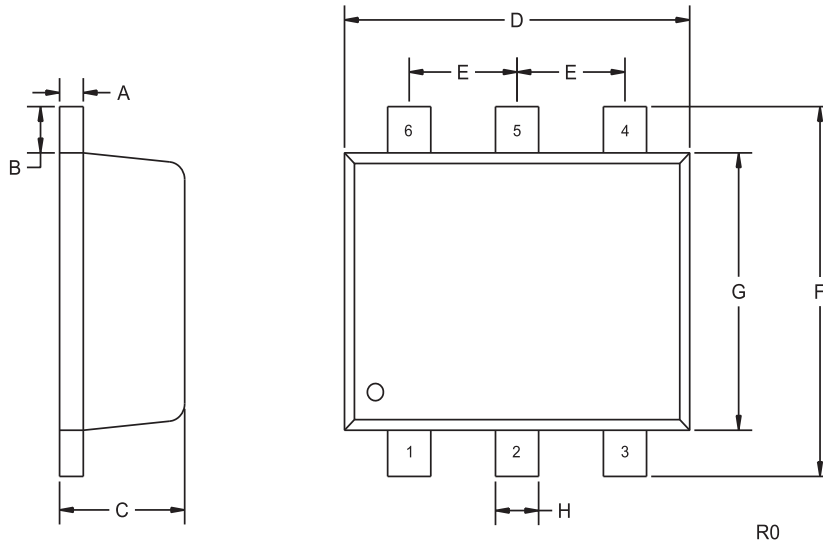
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =50V			300	nA
I _R	V _R =50V, T _A =125°C			100	µA
I _R	V _R =100V			500	nA
BV _R	I _R =100µA	120	150		V
V _F	I _F =1.0mA	0.55	0.59	0.65	V
V _F	I _F =10mA	0.67	0.72	0.77	V
V _F	I _F =100mA	0.85	0.91	1.0	V
C _T	V _R =0, f=1.0MHz			1.5	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω, Rec. to 1.0mA		2.0	4.0	ns

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SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Anode D2
- 4) Cathode D2
- 5) NC
- 6) Cathode D1

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R3 (18-January 2010)